



BUK9Y41-80E,115 Information



For Reference Only

Part Number BUK9Y41-80E,115 **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 80V 24A LFPAK

Package SC-100, SOT-669

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









BUK9Y41-80E,115 Specifications

Manufacturer Part Number BUK9Y41-80E,115 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ± 10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ### 10V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Manufacturer Part Number	BUK9Y41-80E,115
Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Manufacturer	Nexperia USA Inc.
Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-S08 Package / Case SC-100, SOT-669	Category	Discrete Semiconductor Products
Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Bource Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Bov Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 80V 80V 80V 80V 14 (Tc) 11.9nC @ 5V 11.9nC @ 5V 11.9nC @ 5V 1570pF @ 25V 41 mOhm @ 5A, 10V 9 continuous Drain (Id) @ 25°C 175°C (TJ) Surface Mount Supplier Device Package LFPAK56, Power-SO8 SC-100, SOT-669	Package	SC-100, SOT-669
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 80V 80V 80V 80V 24A (Tc) 11.9nC @ 5V 11.9nC @ 5V 11.9nC @ 5V 11.9nC @ 5V 1570pF @ 25V 41nOh 54V 64W (Tc) 41 mOhm @ 5A, 10V 54 mOhm @ 5A, 10V 55°C ~ 175°C (TJ) 80unting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Series	Automotive, AEC-Q101, TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #10V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature Supplier Device Package Package / Case \$C-100, SOT-669	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs All mOhm @ 5A, 10V Operating Temperature Surplier Device Package Package / Case SC-100, SOT-669	Drain to Source Voltage (Vdss)	80V
Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11.9nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Current - Continuous Drain (Id) @ 25°C	24A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs(th) (Max) @ Id	2.1V @ 1mA
Vgs (Max)±10VFET Feature-Power Dissipation (Max)64W (Tc)Rds On (Max) @ Id, Vgs41 mOhm @ 5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	Gate Charge (Qg) (Max) @ Vgs	11.9nC @ 5V
FET Feature - Power Dissipation (Max) 64W (Tc) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Input Capacitance (Ciss) (Max) @ Vds	1570pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 41 mOhm @ 5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs41 mOhm @ 5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Power Dissipation (Max)	64W (Tc)
Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Rds On (Max) @ Id, Vgs	41 mOhm @ 5A, 10V
Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case SC-100, SOT-669	Mounting Type	Surface Mount
	Supplier Device Package	LFPAK56, Power-SO8
Report errors?	Package / Case	SC-100, SOT-669
		Report errors?

BUK9Y41-80E,115 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK9Y41-80E,115 Payment Methods



















BUK9Y41-80E,115 Shipping Methods













If you have any question about BUK9Y41-80E,115, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com